2

Serial No. 10/680,260

Docket No. YOR920030013US1

## **AMENDMENTS TO THE CLAIMS:**

Please cancel claims 3 and 4 without prejudice or disclaimer and amend the claims as follows:

- 1. (Currently Amended) A method of patterning a magnetic thin film, comprising:
  transforming a portion of the magnetic thin film to be non-magnetic and electrically
  insulating using a chemical transformation, said chemical transformation comprises using a
  fluorine-based reactive plasma.
- (Previously Presented) The method of claim 1, further comprising:
   providing a mask over said portion of the magnetic thin film to be preserved using
   photolithography.
- 3-4. (Canceled)
- 5. (Currently Amended) The method of claim [[4]] 1, wherein said fluorine-based reactive plasma comprises any of NF<sub>3</sub>, CF<sub>4</sub>, SF<sub>6</sub>, and CHF<sub>3</sub>.
- 6. (Currently Amended) The method of claim [[3]] 1, wherein a pressure used in said converting transforming is within a range of about 10 mT to about 30 mT.
- 7. (Currently Amended) The method of claim [[3]] 1, wherein said portion of said magnetic thin film comprises any of Ni<sub>0.8</sub>Fe<sub>0.2</sub>, and alloys of nickel, iron, and cobalt, and said converting transforming comprising converting transforming said any of Ni<sub>0.8</sub>Fe<sub>0.2</sub> and alloys of nickel, iron,

Serial No. 10/680,260

Docket No. YOR920030013US1

and cobalt, to a fluorine-containing film.

8. (Original) The method of claim 7, wherein said fluorine-containing film is non-ferromagnetic.

3

- 9. (Original) The method of claim 7, wherein said fluorine-containing film non-magnetic.
- 10. (Original) The method of claim 7, wherein said fluorine-containing film is electrically insulating.
- 11. (Original) The method of claim 2, wherein said mask comprises a photoresist.
- 12. (Original) The method of claim 2, wherein said mask comprises a hard mask patterned layer comprising one of diamond-like carbon (DLC), TiN, and TaN.
- 13. (Previously Presented) The method of claim 1, further comprising: producing a magnetic device.
- 14. (Original) The method of claim 1, wherein said using said chemical transformation is performed at room temperature.
- 15. (Currently Amended) The method of claim [[3]] 1, wherein said reactive plasma includes a fluorocarbon.

Serial No. 10/680,260

Docket No. YOR920030013US1

16. (Currently Amended) The method of claim [[3]] 1, wherein said reactive plasma includes

4

argon.

17. (Currently Amended) The method of claim [[3]] 1, wherein said reactive plasma includes

sulfur hexafluoride.

18. (Currently Amended) The method of claim [[3]] 1, wherein said reactive plasma includes

bromide.

19. (Currently Amended) The method of claim [[4]] 1, wherein a pressure is selectively

employed for said plasma sputtering such that the magnetic thin film material is substantially

free of erosion.

20. (Currently Amended) The method of claim [[3]] 1, further comprising:

forming an insulating layer over the converted portion of said magnetic thin film and said

mask; and

etching said insulating layer and said mask to planarize an upper level of the mask and

the insulating layer.

21. (Original) The method of claim 20, further comprising:

selectively etching said mask; and

forming a conductive material over the insulating layer and an area where the mask was

Serial No. 10/680,260
Docket No. YOR920030013US1
selectively etched.

22. (Currently Amended) The method of claim [[3]] 2, wherein said mask comprises an insulating hard mask, said method further comprising:

after said converting, selectively etching said insulating hard mask to pattern remove said insulating hard mask.

- 23. (Original) The method of claim 22, further comprising:

  forming a conductive material over an area where the insulating hard mask was etched.
- 24. (Currently Amended) The method of claim [[3]] 1, wherein said reactive plasma includes O<sub>2</sub> and a fluorine-containing gas.
- 25. (Currently Amended) The method of claim [[3]] 1, wherein said magnetic thin film includes a magnetic tunnel junction (MTJ), and

wherein after said converting said portion, edges of the magnetic tunnel junction have no exposure to oxygen.

26. (Original) The method of claim 25, wherein an edge smoothness of the MTJ is determined by a line edge roughness of the mask.

27-31. (Canceled)